Supplementary information

Wide Channel Broadband CH$_3$NH$_3$PbI$_3$/SnS Hybrid Photodetector: Breaking the Limit of Bandgap Energy Operation

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Figure S1. A photograph of the device. (a) The cross-shape patterned ITO, (b) SnS on patterned ITO, (c) Perovskite on top of the device.
Figure S2. a) Dark $I-V$ characteristics of the CH$_3$NH$_3$PbI$_3$/SnS device width different channel widths, b) The change in the photocurrent as a function of channel width.